



#### Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	$I_D$
-30V	43mΩ@-10V	-4.2A
	52mΩ@-4.5V	
	72mΩ@-2.5V	

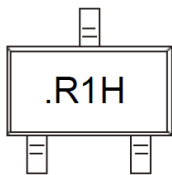
#### Feature

- TrenchFET Power MOSFET
- Exceptional on-resistance and maximum DC current capability

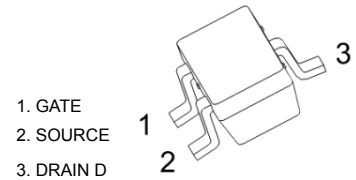
#### Application

- DC/DC Converter
- Load Switch for Portable Devices
- Battery Switch

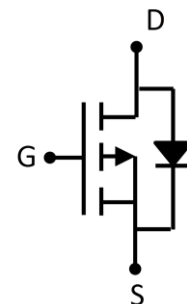
#### MARKING:



#### SOT-23-3L



#### Schematic diagram



#### ABSOLUTE MAXIMUM RATINGS ( $T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Continuous Drain Current	$I_D$	-4.2	A
Pulsed Drain Current <sup>(1)</sup>	$I_{DM}$	21	A
Power Dissipation	$P_D$	1.5	W
Thermal Resistance from Junction to Ambient <sup>(2)</sup>	$R_{\theta JA}$	83.3	$^{\circ}\text{C}/\text{W}$
Junction Temperature	$T_J$	150	$^{\circ}\text{C}$
Storage Temperature	$T_{STG}$	-55~ +150	$^{\circ}\text{C}$

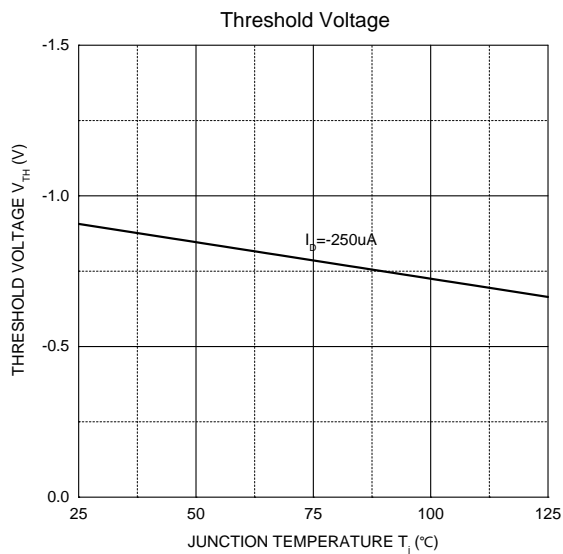
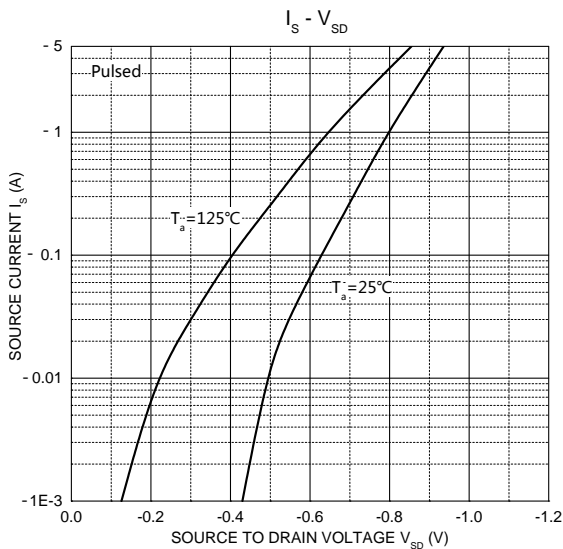
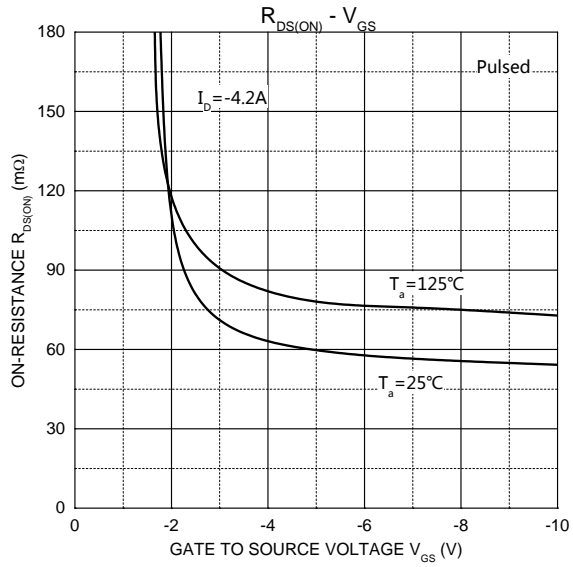
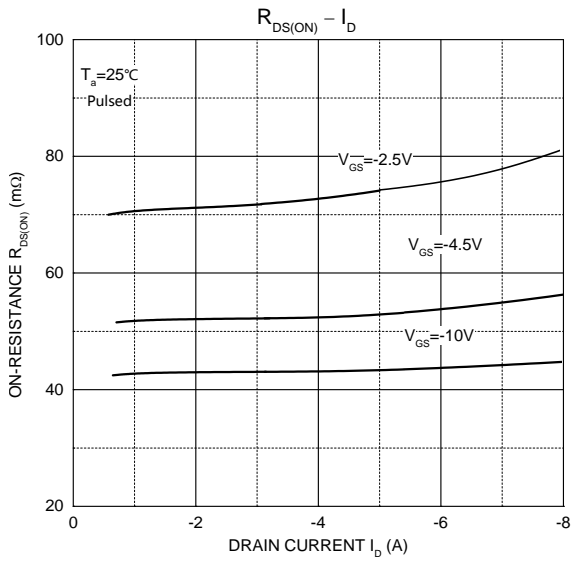
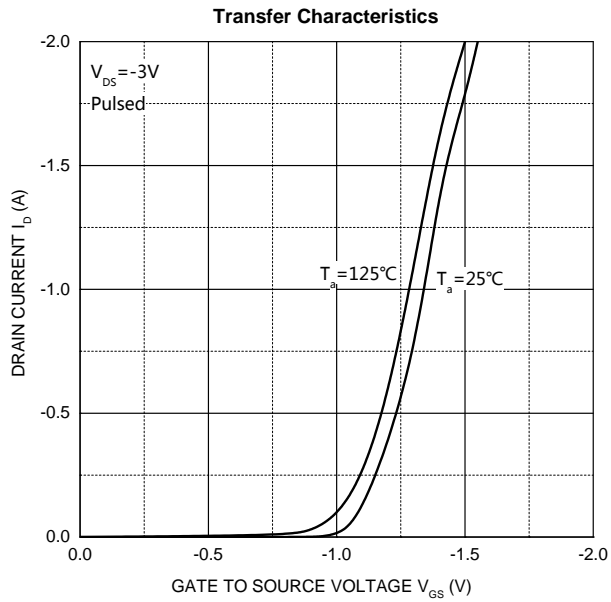
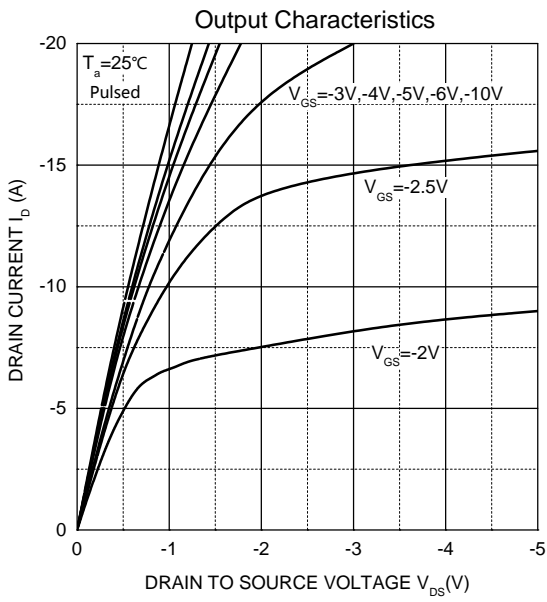
**MOSFET ELECTRICAL CHARACTERISTICS( $T_a=25^{\circ}\text{C}$  unless otherwise noted)**

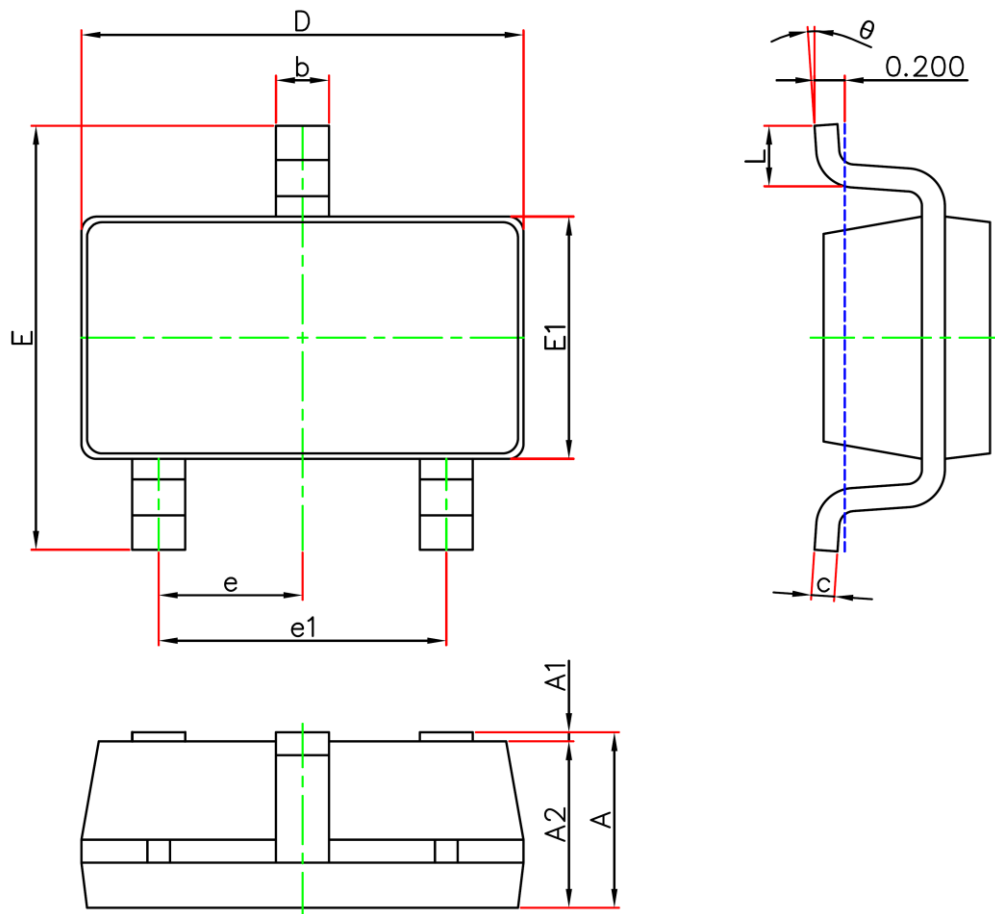
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
<b>Static Characteristics</b>						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-30			V
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = -24V, V_{GS} = 0V$			-1	$\mu A$
Gate-body leakage current	$I_{GSS}$	$V_{GS} = \pm 12V, V_{DS} = 0V$			$\pm 100$	nA
Gate threshold voltage <sup>(3)</sup>	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-0.7	-0.9	-1.3	V
Drain-source on-resistance <sup>(3)</sup>	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -4.0A$		43	65	m $\Omega$
		$V_{GS} = -4.5V, I_D = -3.5A$		52	75	
		$V_{GS} = -2.5V, I_D = -2.5A$		72	90	
Forward transconductance	$g_{FS}$	$V_{DS} = -5V, I_D = -5A$	7			S
<b>Dynamic characteristics<sup>(4)</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = -15V, V_{GS} = 0V, f = 1MHz$		1050		pF
Output Capacitance	$C_{oss}$			127		
Reverse Transfer Capacitance	$C_{rss}$			85		
<b>Switching characteristics<sup>(4)</sup></b>						
Turn-on delay time	$t_{d(on)}$	$V_{GS} = -10V, V_{DS} = -15V,$ $R_L = 3.6\Omega, R_{GEN} = 6\Omega$			6.5	ns
Turn-on rise time	$t_r$				3.5	
Turn-off delay time	$t_{d(off)}$				40	
Turn-off fall time	$t_f$				13	
<b>Source-Drain Diode characteristics</b>						
Diode Forward voltage <sup>(3)</sup>	$V_{DS}$	$V_{GS} = 0V, I_S = -1A$			-1	V

**Notes:**

1. Repetitive Rating : Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t < 5\text{sec}$ .
3. Pulse Test : Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production testing.

**Typical Electrical and Thermal Characteristics**



**SOT-23-3L Package Information**


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0	0.150	0.000	0.006
A2	1.050	1.250	0.041	0.049
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	2.650	2.950	0.104	0.116
E1	1.500	1.700	0.059	0.067
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
$\theta$	0°	8°	0°	8°

单击下面可查看定价，库存，交付和生命周期等信息

[>>GP\(格瑞宝\)](#)